

OA1161
Gold Bonded Germanium Diode

FEATURES

- Low forward voltage drop—low power consumption
- Thirty years of proven reliability—one million hours mean time between failures (MTBF)
- Very low noise level
- Metallurgically bonded

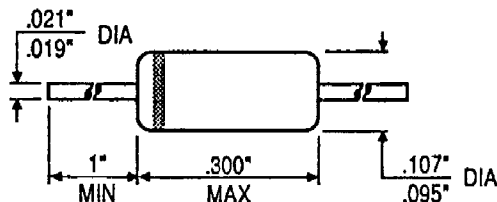
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

| | |
|---------------------------|------------------|
| Peak Inverse Voltage | 140 Volts |
| Peak Forward Current | 500 mA |
| Operating Temperature | - 65 °C to 85 °C |
| Average Power Dissipation | 80 mW |

ELECTRICAL CHARACTERISTICS

| | Symbol | Conditions | Min | Max | Unit | T °C |
|----------------------|--------|------------|-----|-----|---------|-------|
| Peak Inverse Voltage | PIV | 1 mA | 140 | | V | 25 °C |
| Reverse Current | I_r | 100 V | | 55 | μ A | 25 °C |
| Forward Voltage | V_f | 10 mA | | 1.4 | V | 25 °C |

MECHANICAL



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